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Managing Editors

Dr. Claus E. Ascheron

Springer-Verlag GmbH
Tiergartenstr. 17
69121 Heidelberg
Germany
Email: claus.ascheron@springer.com

Dr. Hans J. Koelsch

Springer-Verlag New York, LLC
233, Spring Street
New York, NY 10013
USA
Email: hans.koelsch@springer.com

Assistant Editor

Adelheid H. Duhm

Springer-Verlag GmbH
Tiergartenstr. 17
69121 Heidelberg
Germany
Email: adelheid.duhm@springer.com

David A. Drabold Stefan K. Estreicher (Eds.)

Theory of Defects in Semiconductors

With 60 Figures and 15 Tables

 Springer

David A. Drabold
Department of Physics and Astronomy
Ohio University
Athens, OH 45701, USA
drabold@ohio.edu

Stefan K. Estreicher
Physics Department
Texas Tech University
Lubbock, TX 79409-1051, USA
stefan.estreicher@ttu.edu

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Athens, Ohio,
Lubbock, Texas
February 2006

David A. Drabold
Stefan K. Estreicher

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Believed the Earth stood still,
He never would have blundered so
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He'd then have felt it circulate
And would have learnt to say:
The true way to investigate
Is to drink a bottle a day.

(author unknown)

published in Augustus de Morgan's *A Budget of Paradoxes*, (1866).

Athens, Ohio,
Lubbock, Texas
February 2006

David A. Drabold
Stefan K. Estreicher

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